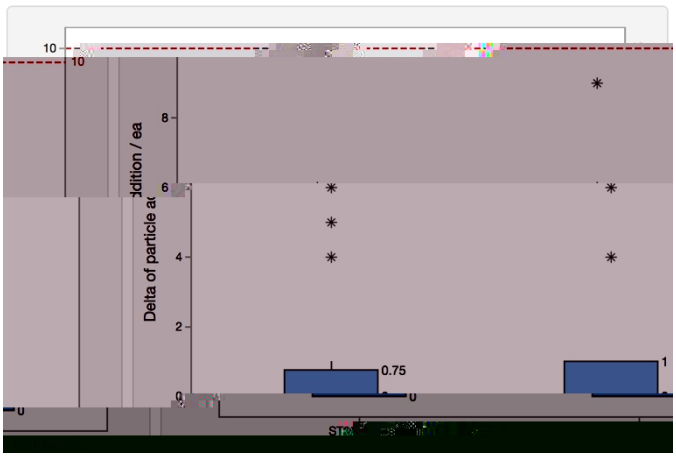
# Development and Application of BEOL Polymer Residue Removal Technology

**Abstract**

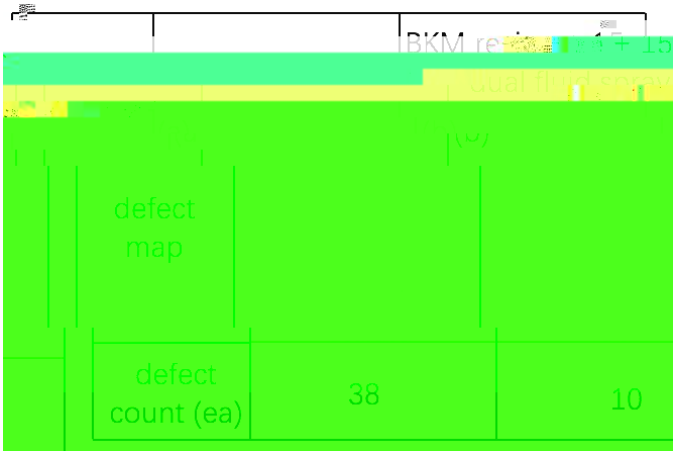
℃

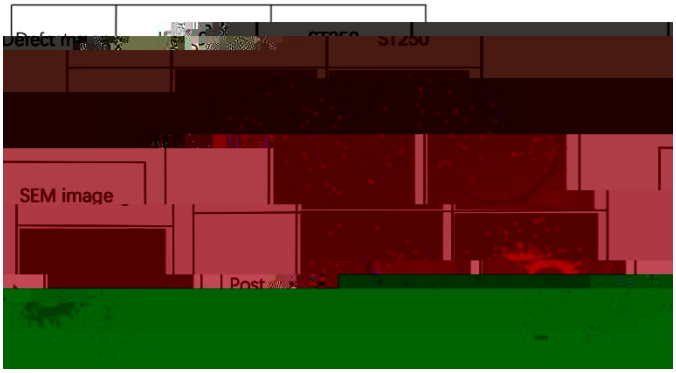
| | ST250 | ICS8000 |
|---|---|---|
| Viscosity at 25℃ (mPa·s) | | |
| Viscosity at 40℃ (mPa·s) | | |

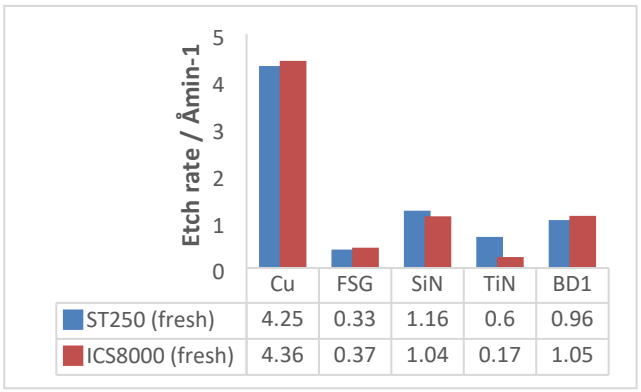
## 1. Introduction



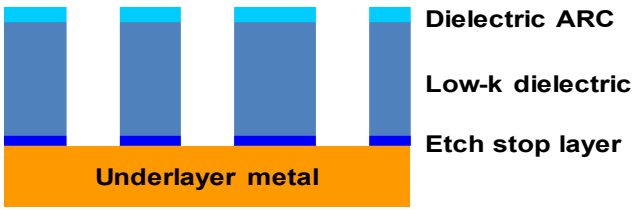

## 2. Experimental and Discussion



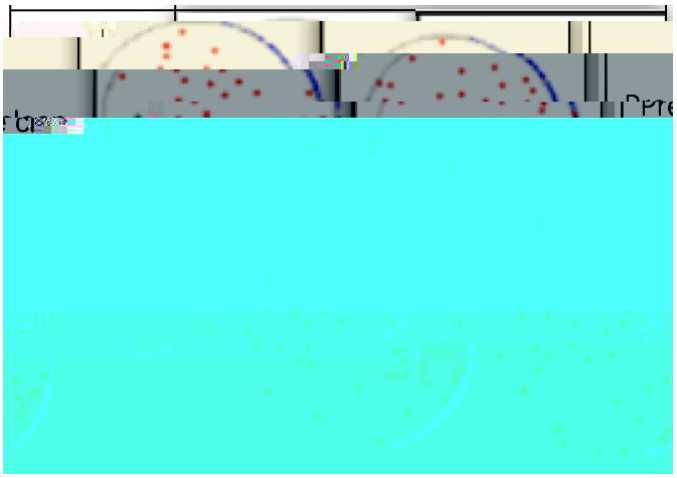

SEM image

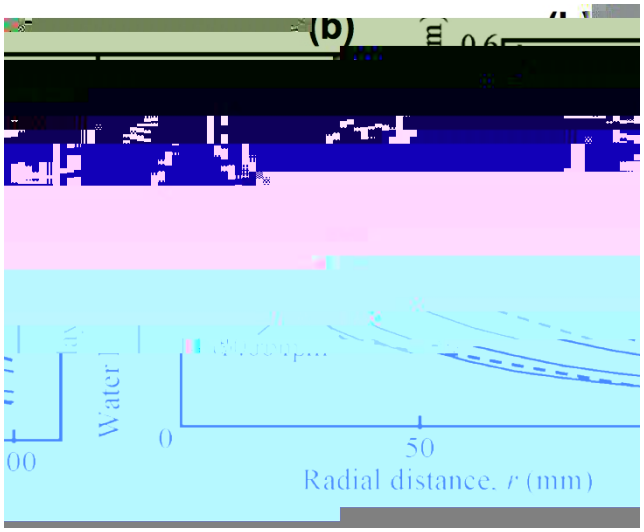

Etch rate / Åmin-1
5
4
3
2
1
0
Cu
FSG
SiN
TiN
BD1
ST250 (fresh) 4.25 0.33 1.16 0.6 0.96
ICS8000 (fresh) 4.36 0.37 1.04 0.17 1.05

℃

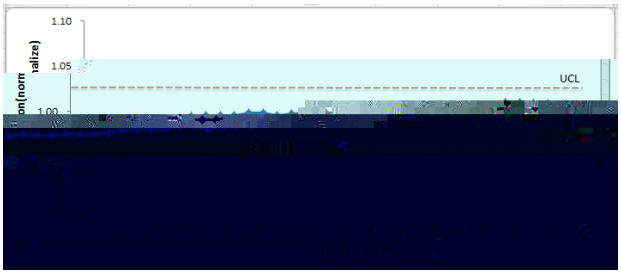

Dielectric ARC
Low-k dielectric
Etch stop layer
Underlayer metal


(a)



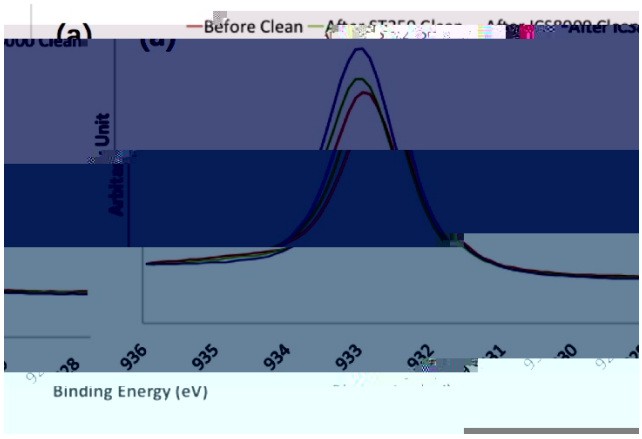

(b)
Water
0
50
Radial distance, r (mm)

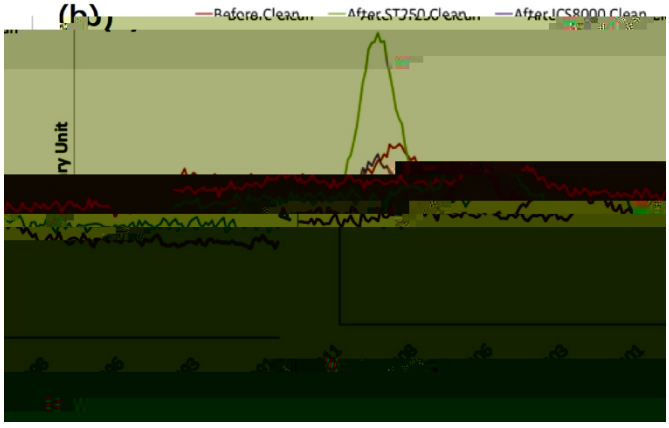

Light
Remaining


1.10
1.05
1.00
UCL

℃

## Acknowledgement




## References

姬峰　王英　铜互连双大马士革结构刻蚀清洗工艺中铜腐蚀失效机理及解决方案研究

## Conclusion